HGTG30N60B3

Data Sheet **November 2013**

600 V, NPT IGBT

The HGTG30N60B3 combines the best features of high input impedance of a MOSFET and the low on-state conduction loss of a bipolar transistor. The IGBT is ideal for many high voltage switching applications operating at moderate frequencies where low conduction losses are essential, such as: UPS, solar inverter and power supplies.

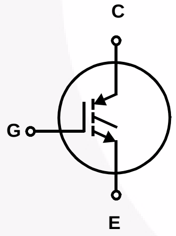
Formerly Developmental Type TA49170.

Ordering Information

PART NUMBER	PACKAGE	BRAND
HGTG30N60B3	TO-247	G30N60B3

NOTE: When ordering, use the entire part number.

Symbol



Features

- 30 A, 600 V, T_C = 110°C
- Low Saturation Voltage: $V_{CE}(sat)$ = 1.45 V @ I_C = 30 A
- Typical Fall Time. . . . . 90ns at T_J = 150°C
- Short Circuit Rating
- Low Conduction Loss

Packaging

JEDEC STYLE TO-247